

Zero-Drift, Rail-to-Rail I/O CMOS Operational Amplifiers

1 Features

- Low Offset Voltage: ±20uV (MAX)
- Input Offset Drift: ±0.1uV/°C (TYP)
- High Gain Bandwidth Product: 11MHz
- Rail-to-Rail Input and Output
- High Gain, CMRR, PSRR:120dB(TYP)
- High Slew Rate: 8.5V/us
- Low Noise: 0.48uVp-p (0.01Hz~10Hz)
- Low Power Consumption: 1.3mA /op amp
- Overload Recovery Time: 0.4us
- Low Supply Voltage: +2.9 V to +5.5 V
- No External Capacitors Required
- Extended Temperature: -40°C to +125°C

2 Applications

- Temperature Sensors
- Medical/Industrial Instrumentation
- Pressure Sensors
- Battery-Powered Instrumentation
- Active Filtering
- Weight Scale Sensor
- Strain Gage Amplifiers
- Power Converter/Inverter

3 Description

The ZM8561, ZM8562, ZM8564 series of CMOS operational amplifiers use auto-zero techniques to simultaneously provide very low offset voltage (20uV max) and near-zero drift over time and temperature. This family of amplifiers has ultralow noise, offset and power.

This miniature, high-precision operational amplifiers offset high input impedance and rail-to-rail input and rail-to-rail output swing. With high gain-bandwidth product of 11MHz and slew rate of 8.5V/us.

Single or dual supplies as low as +2.9V ($\pm 1.45V$) and up to +5.5V ($\pm 2.75V$) may be used.

The ZM8561/ZM8562/ZM8564 are specified for the extended industrial and automotive temperature range (-40°C to 125°C). The ZM8561 single amplifier is available in 5-lead SOT23, 8-lead MSOP8 and 8-lead SOIC packages, The ZM8562 dual amplifier is available in 8-lead SOIC and 8-lead MSOP narrow surface mount packages, The ZM8564 quad is available in 14-lead SOIC and 14-lead narrow TSSOP packages.

Device Information (1)

PART NUMBER	PACKAGE	BODY SIZE (NOM)
	SOT23-5	2.90mm×1.60mm
ZM8561	SOIC-8 (SOP8)	4.90mm×3.90mm
	MSOP-8	3.00mm×3.00mm
7140562	SOIC-8 (SOP8)	4.90mm×3.90mm
ZM8562	MSOP-8	3.00mm×3.00mm
ZM8564	SOIC-14 (SOP14)	8.65mm×3.90mm
	TSSOP-14	5.00mm×4.40mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.

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4 Revision HistoryNote: Page numbers for previous revisions may different from page numbers in the current version.

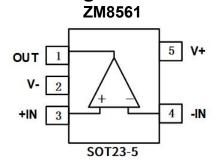
Version	Change Date	Change Item
C.1	2022/05/17	Initial version completed

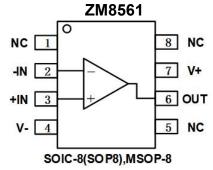
5 Package/Ordering Information⁽¹⁾

Orderable Device	Package Type	Pin	Chan nel	Op Temp(°C)	Device Marking ⁽²⁾	MSL (3)	Package Qty
ZM8561XF	SOT23-5	5	1	-40°C ~125°C	8561	MSL3	Tape and Reel,3000
ZM8561XK	SOIC-8 (SOP8)	8	1	-40°C ~125°C	ZM8561	MSL3	Tape and Reel,4000
ZM8561XM	MSOP-8	8	1	-40°C ~125°C	ZM8561	MSL3	Tape and Reel,4000
ZM8562XK	SOIC-8 (SOP8)	8	2	-40°C ~125°C	ZM8562	MSL3	Tape and Reel,4000
ZM8562XM	MSOP-8	8	2	-40°C ~125°C	ZM8562	MSL3	Tape and Reel,4000
ZM8564XP	SOIC-14(SOP14)	14	4	-40°C ~125°C	ZM8564	MSL3	Tape and Reel,4000
ZM8564XQ	TSSOP-14	14	4	-40°C ~125°C	ZM8564	MSL3	Tape and Reel,4000

- (1) This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the right-hand navigation.
- (2) There may be additional marking, which relates to the lot trace code information (data code and vendor code), the logo or the environmental category on the device.
- (3) The MSL level with using the common preconditioning setting in our assembly factory conforming to the JEDEC industrial standard J-STD-20F.

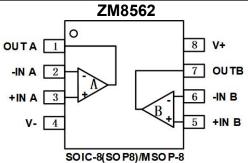
6 Pin Configuration and Functions (Top View)





Pin Description

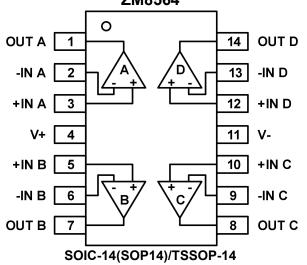
NAME		PIN	I/O	DESCRIPTION
NAME	SOT23-5	SOIC-8 (SOP8)/ MSOP-8	1/0	DESCRIPTION
-IN	4	2	I	Negative (inverting) input
+IN	3	3	I Positive (noninverting) input	
NC	-	1,5,8	-	No internal connection (can be left floating)
OUT	1	6	0	Output
V-	2	4	-	Negative (lowest) power supply
V+	5	7	-	Positive (highest) power supply



Pin Description

NABAT	PIN		PIN		DESCRIPTION
NAME	SOIC-8(SOP8) /MSOP-8	I/O	DESCRIPTION		
-INA	2	I	Inverting input, channel A		
+INA	3	I	Noninverting input, channel A		
-INB	6	I	Inverting input, channel B		
+INB	5	I	Noninverting input, channel B		
OUTA	1	0	Output, channel A		
OUTB	7	0	Output, channel B		
V-	4	-	Negative (lowest) power supply		
V+	8	-	Positive (highest) power supply		

Pin Configuration and Functions (Top View) ZM8564



Pin Description

NAME	PIN	I/O	DESCRIPTION
NAME	SOIC-14 (SOP14)/ TSSOP-14	1/0	DESCRIPTION
-INA	2	I	Inverting input, channel A
+INA	3	I	Noninverting input, channel A
-INB	6	I	Inverting input, channel B
+INB	5	I	Noninverting input, channel B
-INC	9	I	Inverting input, channel C
+INC	10	I	Noninverting input, channel C
-IND	13	I	Inverting input, channel D
+IND	12	I	Noninverting input, channel D
OUTA	1	0	Output, channel A
OUTB	7	0	Output, channel B
OUTC	8	0	Output, channel C
OUTD	14	0	Output, channel D
V-	11	-	Negative (lowest) power supply
V+	4	-	Positive (highest) power supply

7 Specifications

7.1 Absolute Maximum Ratings

Over operating free-air temperature range (unless otherwise noted) (1)

			MIN	MAX	UNIT
	Supply, V _S =(V+) – (V-)			7	
Voltage	Signal input pin (2)		(V-)-0.5	(V+) +0.5	V
	Signal output pin (3)		(V-)-0.5	(V+) +0.5	
	Signal input pin (2)		-10	10	mA
Current	Signal output pin (3)	Signal output pin (3)		55	mA
	Output short-circuit (4)		Conti	nuous	
		SOT23-5		230	
		SOIC-8(SOP8)		110	
θ_{JA}	Package thermal impedance (5)	MSOP-8		170	°C/W
		SOIC-14(SOP14)		105	
		TSSOP-14		90	
Operating range, T _A		•	-40	125	
Temperature	Junction, T _J		-40	150	°C
	Storage, T _{stg}		-65	150	1

⁽¹⁾Stresses above these ratings may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those specified is not implied.

⁽²⁾Input terminals are diode-clamped to the power-supply rails. Input signals that can swing more than 0.5V beyond the supply rails should be current-limited to 10mA or less.

⁽³⁾Output terminals are diode-clamped to the power-supply rails. Output signals that can swing more than 0.5V beyond the supply rails should be current-limited to ±50mA or less.

⁽⁴⁾Short-circuit to ground, one amplifier per package.

⁽⁵⁾The package thermal impedance is calculated in accordance with JESD-51.

⁽⁶⁾The maximum power dissipation is a function of $T_{J(MAX)}$, R_{8JA} , and T_A . The maximum allowable power dissipation at any ambient temperature is $P_D = (T_{J(MAX)} - T_A) / R_{8JA}$. All numbers apply for packages soldered directly onto a PCB.



7.2 ESD Ratings

			VALUE	UNIT
V/===>	Electrostatic	Human-body model (HBM)	±5000	
V(ESD)	discharge	Machine Model (MM)	±400	\ \ \ \ \



ESD SENSITIVITY CAUTION

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

7.3 Recommended Operating Conditions

Over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
Supply voltage Ve= (V+) (V)	Single-supply	2.7		5.5	\/
Supply voltage, Vs= (V+) - (V-)	Dual-supply	±1.35		±2.75	\ \ \



7.4 Electrical Characteristics

Boldface limits apply over the specified temperature range, T_A = -40°C to +125°C. (At T_A = +25°C, V_S =5V, R_L = 10k Ω connected to V_S /2, and V_{OUT} = V_S /2, unless otherwise noted.)

	0)/41701		ZM85	61, ZM8	3562, ZM8	564
PARAMETER	SYMBOL	CONDITION	MIN	TYP	MAX	UNIT
OFFSET VOLTAGE						
Input Offset Voltage	Vos	V _{CM} = V _S /2	-20	±3	20	uV
Input Offset Voltage Average Drift	Vos Tc			±0.1	±0.4	uV/°C
Power-Supply Rejection Ratio	PSRR	V_S = +2.9V to +5.5V, V_{CM} = 0	100	120		dB
Channel Separation, dc				0.1		uV/V
INPUT BIAS CURRENT				•	•	
Input Bias Current	IB	V _{CM} = V _S /2		±100		pА
Input Offset Current	los			±10		pА
NOISE PERFORMANCE						
Input Voltage Noise	e _n p-p	f= 0.01Hz to 10Hz		0.48		uVpp
Input Voltage Noise	e _n p-p	f= 0.01Hz to 1Hz		0.15		uVpp
Input Voltage Noise Density	e _n	f= 1KHz		32		nV/√Hz
Input Current Noise Density	in	f= 10Hz		1.5		fA/√Hz
INPUT VOLTAGE RANGE	'		'		'	
Common-Mode Voltage Range	V _{CM}		(V-) -0.1		(V+) +0.1	V
Common-Mode Rejection Ratio	CMRR	$(V-) -0.1V < V_{CM} < (V+) + 0.1V$	100	120		dB
INPUT CAPACITANCE			1			
Differential				5		pF
Common-Mode				5		pF
Open-Loop Gain						
Open-Loop Voltage Gain	A _{OL}	R_L = 10K Ω , V_O = 0.3V to 4.7V, T_A = -40°C to 125°C	100	120		dB
DYNAMIC PERFORMANCE						
Slew Rate	SR	G= +1		8.5		V/us
Gain-Bandwidth Product	GBW			11		MHz
Overload Recovery Time	t _{OR}			0.4		us
OUTPUT CHARACTERISTICS						
Output Voltage High	V _{OH}	R_L =100 K Ω to GND	4.99	4.998		V
Output voltage riigh	VOH	R_L =10 K Ω to GND	4.95	4.98		V
Output Voltage Low	V _{OL}	R_L =100 K Ω to V+		1	10	mV
Output Voltage Low	VOL	R_L =10 K Ω to V+		10	30	IIIV
Short-Circuit Current	Isc			65		mA
POWER SUPPLY						
Operating Voltage Range	Vs		2.9		5.5	V
Quiescent Current/ Amplifier	lα			1.3	1.55	mA
SHUTDOWN						
toff				2		us
ton				150		us

V _L (shutdown)	0	+0.8	V
V _H (amplifier is active)	0.75 (V+)	V+	V
Input Bias Current of Enable Pin	50)	pА
I _{QSD}	1	5	uA

7.5 Typical Characteristics

NOTE: The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only.

At T_A = +25°C, V_S =5V, R_L = 10k Ω connected to $V_S/2$, V_{OUT} = $V_S/2$, unless otherwise noted.

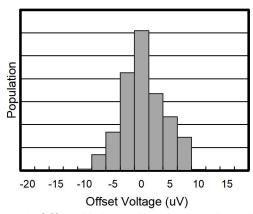


Figure 1. Offset Voltage Production Distribution

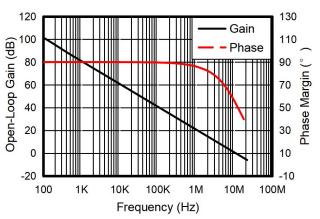


Figure 3. Open-Loop Gain and Phase vs Frequency

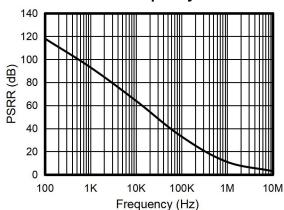


Figure 5. Power-Supply Rejection Ratio vs Frequency

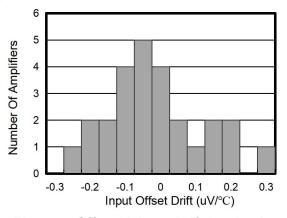


Figure 2. Offset Voltage Drift Production Distribution

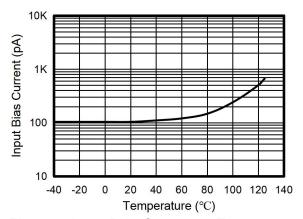


Figure 4. Input Bias Current vs Temperature

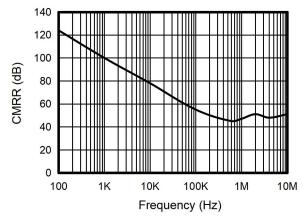


Figure 6. Common-Mode Rejection Ratio vs Frequency

Typical Characteristics

NOTE: The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only.

At T_A = +25°C, V_S =5V, R_L = 10k Ω connected to $V_S/2$, V_{OUT} = $V_S/2$, unless otherwise noted.

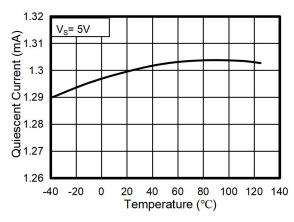


Figure 7. Quiescent Current vs Temperature

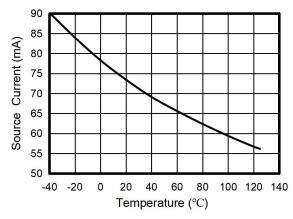


Figure 9. Source Current vs Temperature

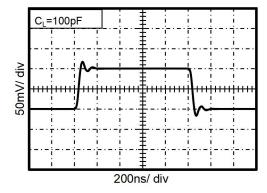


Figure 11. Small-Signal Step Response

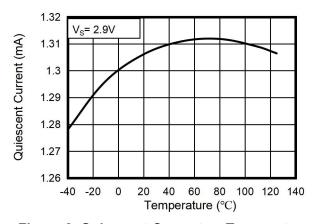


Figure 8. Quiescent Current vs Temperature

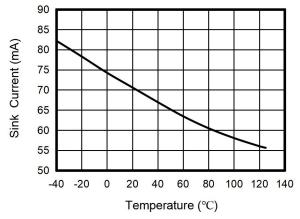


Figure 10. Sink Current vs Temperature

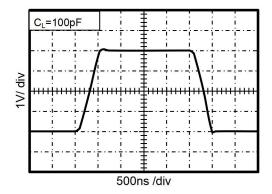
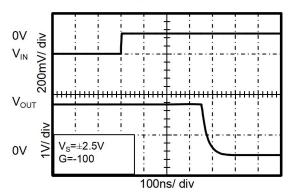


Figure 12. Large-Signal Step Response

Typical Characteristics

NOTE: The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only.

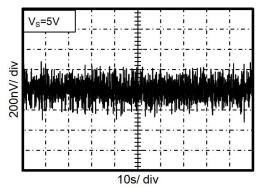
At T_A = +25°C, V_S =5V, R_L = 10k Ω connected to $V_S/2$, V_{OUT} = $V_S/2$, unless otherwise noted.



V_{IN} 0V N_{OUT} V_S=±2.5V G=-100 V_S=±2.5V G=-

Figure 13. Positive Overvoltage Recovery

Figure 14. Negative Overvoltage Recovery



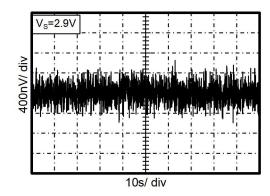
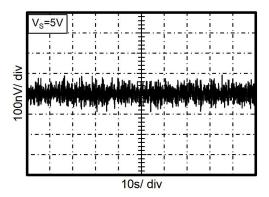


Figure 15. 0.01Hz to 10Hz Noise

Figure 16. 0.01Hz to 10Hz Noise



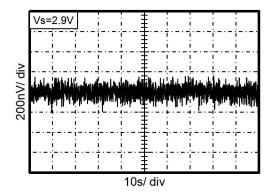


Figure 17. 0.01Hz to 1Hz Noise

Figure 18. 0.01Hz to 1Hz Noise

8 Detailed Description

8.1 Overview

The ZM8561, ZM8562, ZM8564 series op amps are unity-gain stable and free from unexpected output phase reversal. They use auto-zeroing techniques to provide low offset voltage and very low drift over time and temperature.

Good layout practice mandates use of a 0.1µF capacitor placed closely across the supply pins.

For lowest offset voltage and precision performance, circuit layout and mechanical conditions should be optimized. Avoid temperature gradients that create thermoelectric (Seebeck) effects in thermocouple junctions formed from connecting dissimilar conductors. These thermally-generated potentials can be made to cancel by assuring that they are equal on both input terminals.

- Use low thermoelectric-coefficient connections (avoid dissimilar metals).
- Thermally isolate components from power supplies or other heat-sources.
- · Shield op amp and input circuitry from air currents, such as cooling fans.

Following these guidelines will reduce the likelihood of junctions being at different temperatures, which can cause thermoelectric voltages of 0.1µV/°C or higher, depending on materials used.

8.2 Operating Volatage

The ZM8561, ZM8562, ZM8563, ZM8564 series op amps operate over a power-supply range of +2.9V to +5.5V (±1.45V to ±2.75V). Supply voltages higher than 7V (absolute maximum) can permanently damage the amplifier. Parameters that vary over supply voltage or temperature are shown in the typical characteristics section of this data sheet.

9 Application Note

The ZM856X is a unity-gain stable, precision operational amplifier with very low offset voltage drift; these devices are also free from output phase reversal. Applications with noisy or high-impedance power supplies require decoupling capacitors close to the device power-supply pins. In most cases, 0.1-uF capacitors are adequate.

Typical Applications

9.1Bidirectional Current-Sensing

This single-supply, low-side, bidirectional current-sensing solution detects load currents from -1 A to 1 A. The single-ended output spans from 110 mV to 3.19 V. This design uses the ZM856X because of its low offset voltage and rail-to-rail input and output. One of the amplifiers is configured as a difference amplifier and the other provides the reference voltage.

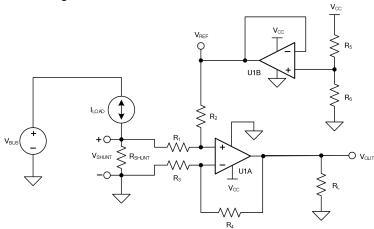


Figure 19. Bidirectional Current-Sensing Schematic

9.2 Design Requirements

This solution has the following requirements:

Supply voltage: 3.3 V

• Input: -1 A to 1 A

 \bullet Output: 1.65 V ±1.54 V (110 mV to 3.19 V)

9.3 Detailed Design Procedure

The load current, I_{LOAD} , flows through the shunt resistor (R_{SHUNT}) to develop the shunt voltage, V_{SHUNT} . The shunt voltage is then amplified by the difference amplifier, which consists of U1A and R_1 through R_4 . The gain of the difference amplifier is set by the ratio of R_4 to R_3 . To minimize errors, set $R_2 = R_4$ and $R_1 = R_3$. The reference voltage, V_{REF} , is supplied by buffering a resistor divider using U1B. The transfer function is given by Equation 1.

Vout= V_{SHUNT} × Gain _{Diff Amp} + V_{REF}

Where

 $V_{SHUNT}=I_{LOAD}\times R_{SHUNT}$

$$Gain_{Diff_Amp} = \frac{R_4}{R_3}$$

$$V_{REF} = V_{CC} \times \left[\frac{R_6}{R_5 + R_6} \right]$$

(1)

There are two types of errors in this design: offset and gain. Gain errors are introduced by the tolerance of the shunt resistor and the ratios of R_4 to R_3 and, similarly, R_2 to R_1 . Offset errors are introduced by the voltage divider (R_5 and R_6) and how closely the ratio of R_4/R_3 matches R_2/R_1 . The latter value impacts the CMRR of the difference amplifier, which ultimately translates to an offset error. Because this is a low-side measurement, the value of V_{SHUNT} is the ground potential for the system load. Therefore, it is important to place a maximum

value on V_{SHUNT} . In this design, the maximum value for V_{SHUNT} is set to 100 mV. Equation 2 calculates the maximum value of the shunt resistor given a maximum shunt voltage of 100 mV and maximum load current of 1 A.

$$R_{SHUNT(Max)} = \frac{V_{SHUNT(Max)}}{I_{LOAD(Max)}} = \frac{100 \text{ mV}}{1 \text{ A}} = 100 \text{ m}\Omega$$
(2)

9.4 Application Note

The tolerance of R_{SHUNT} is directly proportional to cost. For this design, a shunt resistor with a tolerance of 0.5% was selected. If greater accuracy is required, select a 0.1% resistor or better.

The load current is bidirectional; therefore, the shunt voltage range is -100 mV to 100 mV. This voltage is divided down by R_1 and R_2 before reaching the operational amplifier, U1A. Take care to ensure that the voltage present at the noninverting node of U1A is within the common-mode range of the device. Therefore, it is important to use an operational amplifier, such as the ZM856X, that has a common-mode range that extends below the negative supply voltage. Finally, to minimize offset error, note that the ZM856X has a typical offset voltage of $\pm 3\mu V$ ($\pm 20\mu V$ maximum). Given a symmetric load current of -1 A to 1 A, the voltage divider resistors (R_5 and R_6) must be equal. To be consistent with the shunt resistor, a tolerance of 0.5% was selected. To minimize power consumption, ± 1000 resistors were used. To set the gain of the difference amplifier, the common-mode range and output swing of the ZM856X must be considered. Equation 3 and Equation 4 depict the typical common-mode range and maximum output swing, respectively, of the ZM856X given a 3.3V supply.

$$-100 \text{mV} < \text{V}_{\text{CM}} < 3.4 \text{V} \tag{3}$$

$$100 \text{mV} < \text{V}_{\text{OUT}} < 3.2 \text{V} \tag{4}$$

The gain of the difference amplifier can now be calculated as shown in Equation 5.

$$Gain_{Diff_Amp} = \frac{V_{OUT_Max} - V_{OUT_Min}}{R_{SHUNT} \times (I_{MAX} - I_{MIN})} = \frac{3.2 \text{ V} - 100 \text{ mV}}{100 \text{ m}\Omega \times [1 \text{ A} - (-1 \text{A})]} = 15.5 \frac{\text{V}}{\text{V}}$$
(5)

The resistor value selected for R_1 and R_3 was $1k\Omega$. $15.4k\Omega$ was selected for R_2 and R_4 because it is the nearest standard value. Therefore, the ideal gain of the difference amplifier is 15.4 V/V.

The gain error of the circuit primarily depends on R_1 through R_4 . As a result of this dependence, 0.1% resistors were selected. This configuration reduces the likelihood that the design requires a two-point calibration. A simple one-point calibration, if desired, removes the offset errors introduced by the 0.5% resistors.

9.5 Application Curve

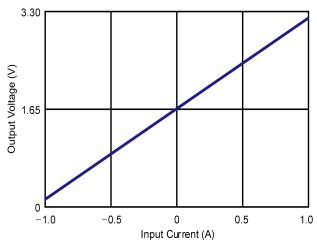


Figure 20. Bidirectional Current-Sensing Circuit Performance: Output Voltage vs Input Current

10 Layout

10.1 Layout Guidelines

Attention to good layout practices is always recommended. Keep traces short. When possible, use a PCB ground plane with surface-mount components placed as close to the device pins as possible. Place a 0.1uF capacitor closely across the supply pins.

These guidelines should be applied throughout the analog circuit to improve performance and provide benefits such as reducing the EMI susceptibility.

10.2 Layout Example

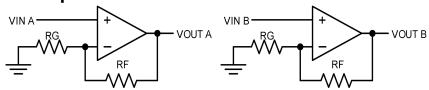


Figure 21. Schematic Representation

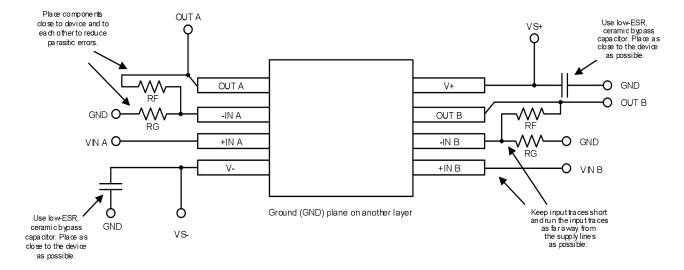
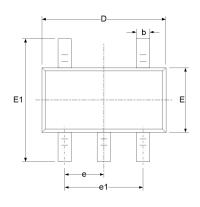
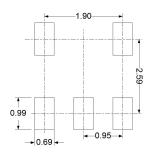


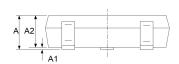
Figure 22. Layout Example

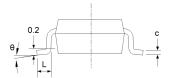
11 Pacakage Outline Dimensions SOT23-5





RECOMMENDED LAND PATTERN (Unit: mm)

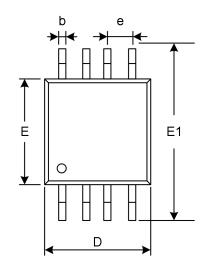


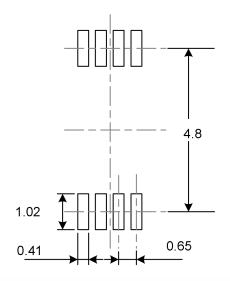


Symbol	Dimensions I	n Millimeters	Dimensions In Inches			
	Min	Max	Min	Max		
А	1.050	1.250	0.041	0.049		
A1	0.000	0.100	0.000	0.004		
A2	1.050	1.150	0.041	0.045		
b	0.300	0.500	0.012	0.020		
С	0.100	0.200	0.004	0.008		
D	2.820	3.020	0.111	0.119		
E	1.500	1.700	0.059	0.067		
E1	2.650	2.950	0.104	0.116		
е	0.950	(BSC)	0.037 (BSC)			
e1	1.800	2.000	0.071	0.079		
L	0.300	0.600	0.012	0.024		
θ	0°	8°	0°	8°		

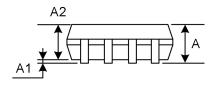
- A. This drawing is subject to change without notice.
 B. Plastic or metal protrusions of 0.15mm maximum per side are not included.
 C. BSC: Basic Dimension. Theoretically exact value shown without tolerances.

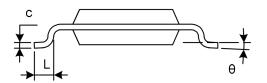
MSOP-8





RECOMMENDED LAND PATTERN (Unit: mm)





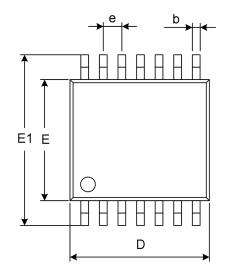
Symbol	Dimensions	In Millimeters	Dimensions In Inches			
	Min	Max	Min	Max		
А	0.820	1.100	0.032	0.043		
A1	0.020	0.150	0.001	0.006		
A2	0.750	0.950	0.030	0.037		
b	0.250	0.380	0.010	0.015		
С	0.090	0.230	0.004	0.009		
D	2.900	3.100	0.114	0.122		
е	0.650	(BSC)	0.026 (BSC)			
E	2.900	3.100	0.114	0.122		
E1	4.750	5.050	0.187	0.199		
L	0.400	0.800	0.016	0.031		
θ	0°	6°	0°	6°		

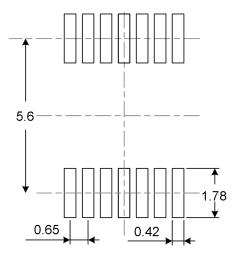
- A. This drawing is subject to change without notice.

 B. Plastic or metal protrusions of 0.15mm maximum per side are not included.

 C. BSC: Basic Dimension. Theoretically exact value shown without tolerances.

TSSOP-14





RECOMMENDED LAND PATTERN (Unit: mm)

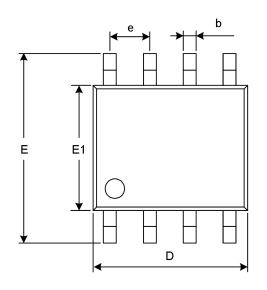


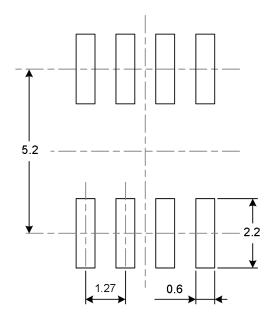


Symbol	Dimensions I	n Millimeters	Dimensions In Inches			
	Min	Max	Min	Max		
А		1.200		0.047		
A1	0.050	0.150	0.002	0.006		
A2	0.800	1.050	0.031	0.041		
b	0.190	0.300	0.007	0.012		
С	0.090	0.200	0.004	0.008		
D	4.860	5.100	0.191	0.201		
E	4.300	4.500	0.169	0.177		
E1	6.250	6.550	0.246	0.258		
е	0.650	(BSC)	0.026 (BSC)			
L	0.500	0.700	0.020	0.028		
Н	0.25 (TYP)		0.01 (TYP)			
θ	1°	7°	1°	7°		

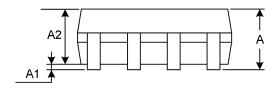
- A. This drawing is subject to change without notice.
 B. Plastic or metal protrusions of 0.15mm maximum per side are not included.
 C. BSC: Basic Dimension. Theoretically exact value shown without tolerances.

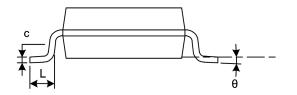
SOIC-8 (SOP8)





RECOMMENDED LAND PATTERN (Unit: mm)



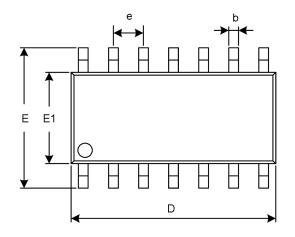


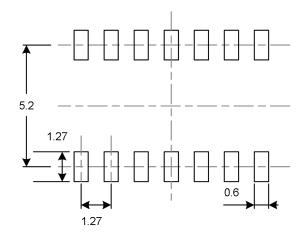
Symbol	Dimensions I	n Millimeters	Dimensions In Inches			
	Min	Max	Min	Max		
А	1.350	1.750	0.053	0.069		
A1	0.100	0.250	0.004	0.010		
A2	1.350	1.550	0.053	0.061		
b	0.330	0.510	0.013	0.020		
С	0.170	0.250	0.007	0.010		
D	4.800	5.000	0.189	0.197		
е	1.270	(BSC)	0.050 (BSC)			
Е	5.800	6.200	0.228	0.244		
E1	3.800	4.000	0.150	0.157		
L	0.400	1.270	0.016	0.050		
θ	0°	8°	0°	8°		

- A. This drawing is subject to change without notice.

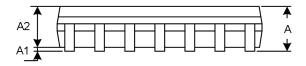
 B. Plastic or metal protrusions of 0.15mm maximum per side are not included.
- C. BSC: Basic Dimension. Theoretically exact value shown without tolerances.

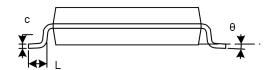
SOIC-14 (SOP14)





RECOMMENDED LAND PATTERN (Unit: mm)



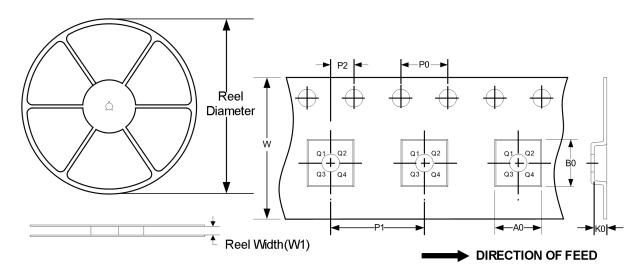


Symbol	Dimensions I	n Millimeters	Dimensions In Inches			
	Min	Max	Min	Max		
Α	1.350	1.750	0.053	0.069		
A1	0.100	0.250	0.004	0.010		
A2	1.350	1.550	0.053	0.061		
b	0.310	0.510	0.012	0.020		
С	0.100	0.250	0.004	0.010		
D	8.450	8.850	0.333	0.348		
е	1.270	(BSC)	0.050 (BSC)			
E	5.800	6.200	0.228	0.244		
E1	3.800	4.000	0.150	0.157		
L	0.400	1.270	0.016	0.050		
θ	0°	8°	0°	8°		

- A. This drawing is subject to change without notice.
 B. Plastic or metal protrusions of 0.15mm maximum per side are not included.
 C. BSC: Basic Dimension. Theoretically exact value shown without tolerances.

12 Tape and Reel Information REEL DIMENSIONS

TAPE DIMENSION



NOTE: The picture is only for reference. Please make the object as the standard.

KEY PARAMETER LIST OF TAPE AND REEL

Package Type	Reel	Reel Width	A0	B0	K0	P0	P1	P2	W	Pin1
	Diameter	(mm)	(mm)	(mm)	(mm)	(mm)	(mm)	(mm)	(mm)	Quadrant
SOT23-5	7"	9.5	3.20	3.20	1.40	4.0	4.0	2.0	8.0	Q3
MSOP-8	13"	12.4	5.20	3.30	1.50	4.0	8.0	2.0	12.0	Q1
TSSOP-14	13"	12.4	6.95	5.60	1.20	4.0	8.0	2.0	12.0	Q1
SOIC-8 (SOP8)	13"	12.4	6.40	5.40	2.10	4.0	8.0	2.0	12.0	Q1
SOIC-14 (SOP14)	13"	16.4	6.60	9.30	2.10	4.0	8.0	2.0	16.0	Q1

^{1.} All dimensions are nominal.

^{2.} Plastic or metal protrusions of 0.15mm maximum per side are not included.



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